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(54) Title: RESIDUAL LIQUID METAL TREATMENT DURING LED FABRICATION

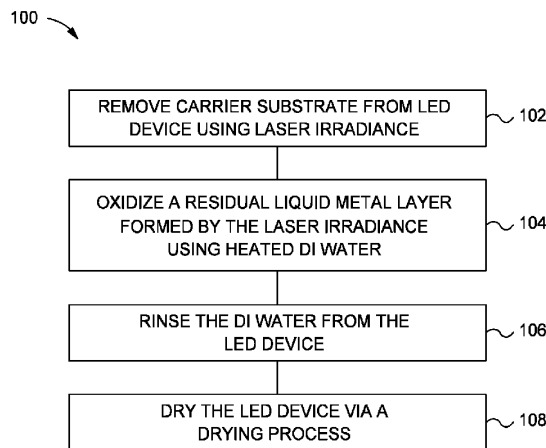


FIG. 1

(57) Abstract: The present disclosure generally includes a method for forming a light emitting diode (LED) device, that includes using laser irradiation to remove a carrier substrate from the LED device, oxidizing a residual liquid metal layer formed by the laser irradiation by soaking the LED device in heated de-ionized water, rinsing the de-ionized water off the LED device, and drying the LED device using a drying process.

[Continued on next page]

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